

# NSS1C200MZ4

## 100 V, 2.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are miniature surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	-100	Vdc
Collector-Base Voltage	$V_{CB}$	-140	Vdc
Emitter-Base Voltage	$V_{EB}$	-7.0	Vdc
Base Current – Continuous	$I_B$	1.0	Adc
Collector Current – Continuous – Peak	$I_C$	2.0 3.0	Adc
Total Power Dissipation Total $P_D$ @ $T_A = 25^\circ\text{C}$ (Note 1) Total $P_D$ @ $T_A = 25^\circ\text{C}$ (Note 2)	$P_D$	2.0 0.8	W
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta JA}$	64 155	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	$T_L$	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

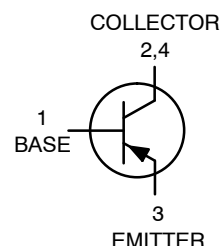
1. mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material
2. mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material



ON Semiconductor®

<http://onsemi.com>

## -100 VOLTS, 2.0 AMPS PNP LOW $V_{CE(sat)}$ TRANSISTOR

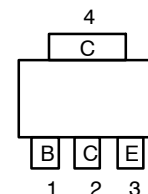


### MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- 1C200 = Specific Device Code
- = Pb-Free Package

### PIN ASSIGNMENT



Top View Pinout

### ORDERING INFORMATION

Device	Package	Shipping†
NSS1C200T1G	SOT-223 (Pb-Free)	1000/ Tape & Reel
NSS1C200T3G	SOT-223 (Pb-Free)	4000/ Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NSS1C200MZ4

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = –10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	–100			Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = –0.1 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	–140			Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = –0.1 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	–7.0			Vdc
Collector Cutoff Current (V <sub>CB</sub> = –140 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>			–100	nAdc
Emitter Cutoff Current (V <sub>EB</sub> = –6.0 Vdc)	I <sub>EBO</sub>			–50	nAdc

## ON CHARACTERISTICS

DC Current Gain (Note 3) (I <sub>C</sub> = –10 mA, V <sub>CE</sub> = –2.0 V) (I <sub>C</sub> = –500 mA, V <sub>CE</sub> = –2.0 V) (I <sub>C</sub> = –1.0 A, V <sub>CE</sub> = –2.0 V) (I <sub>C</sub> = –2.0 A, V <sub>CE</sub> = –2.0 V)	h <sub>FE</sub>	150 120 80 50		360	
Collector–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = –0.1 A, I <sub>B</sub> = –0.010 A) (I <sub>C</sub> = –0.5 A, I <sub>B</sub> = –0.050 A) (I <sub>C</sub> = –1.0 A, I <sub>B</sub> = –0.100 A) (I <sub>C</sub> = –2.0 A, I <sub>B</sub> = –0.200 A)	V <sub>CE(sat)</sub>			–0.040 –0.080 –0.125 –0.220	V
Base–Emitter Saturation Voltage (Note 3) (I <sub>C</sub> = –1.0 A, I <sub>B</sub> = –0.100 A)	V <sub>BE(sat)</sub>			–0.950	V
Base–Emitter Turn–on Voltage (Note 3) (I <sub>C</sub> = –1.0 A, V <sub>CE</sub> = –2.0 V)	V <sub>BE(on)</sub>			–0.850	V
Cutoff Frequency (I <sub>C</sub> = –100 mA, V <sub>CE</sub> = –5.0 V, f = 100 MHz)	f <sub>T</sub>		120		MHz
Input Capacitance (V <sub>EB</sub> = 3.0 V, f = 1.0 MHz)	C <sub>ibo</sub>		200		pF
Output Capacitance (V <sub>CB</sub> = 10 V, f = 1.0 MHz)	C <sub>obo</sub>		22		pF

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

## TYPICAL CHARACTERISTICS

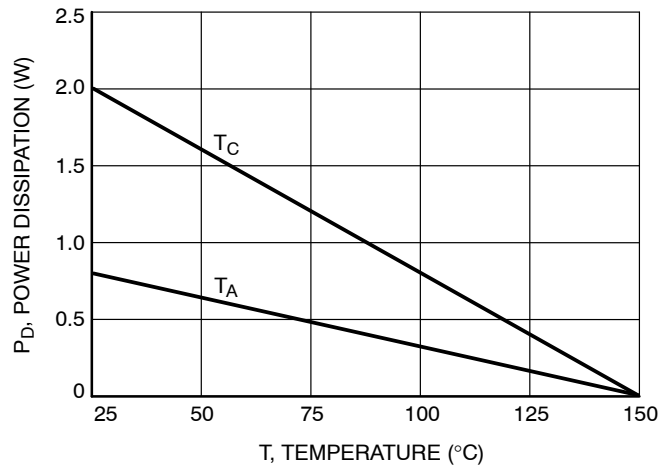


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

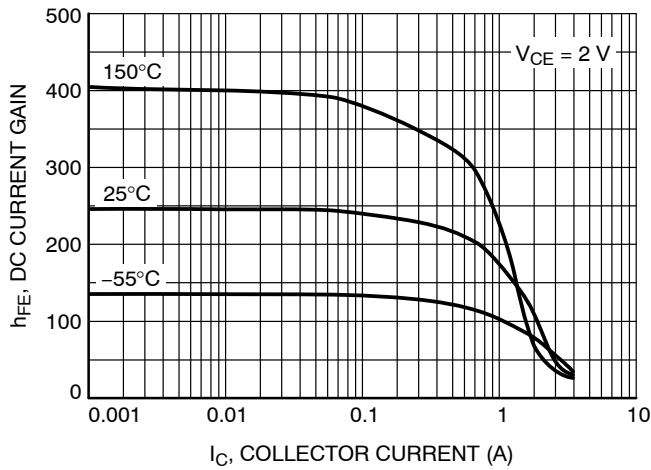


Figure 2. DC Current Gain

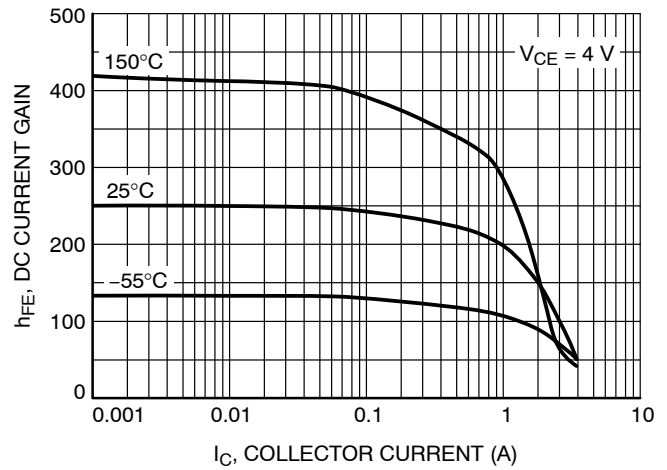


Figure 3. DC Current Gain

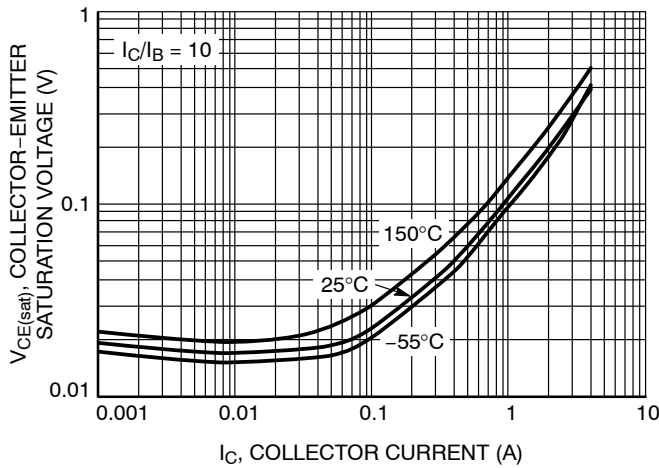


Figure 4. Collector-Emitter Saturation Voltage

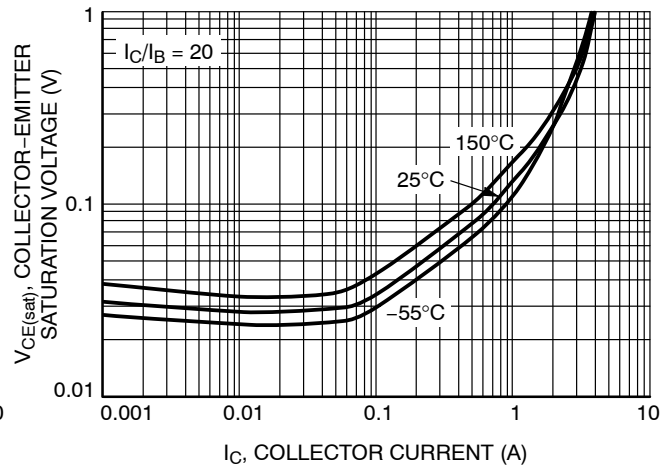


Figure 5. Collector-Emitter Saturation Voltage

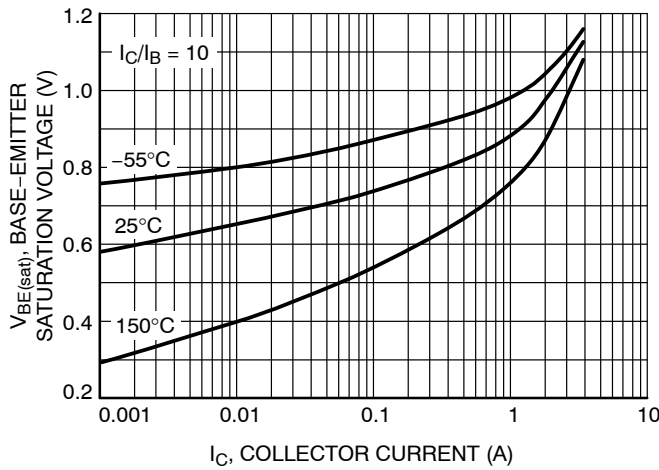


Figure 6. Base-Emitter Saturation Voltage

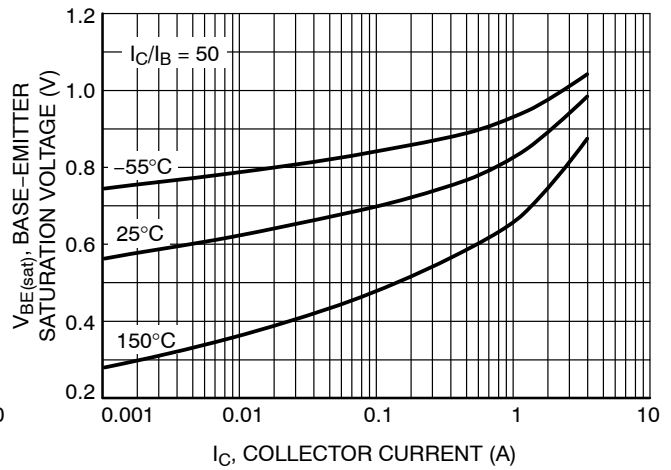


Figure 7. Base-Emitter Saturation Voltage

TYPICAL CHARACTERISTICS

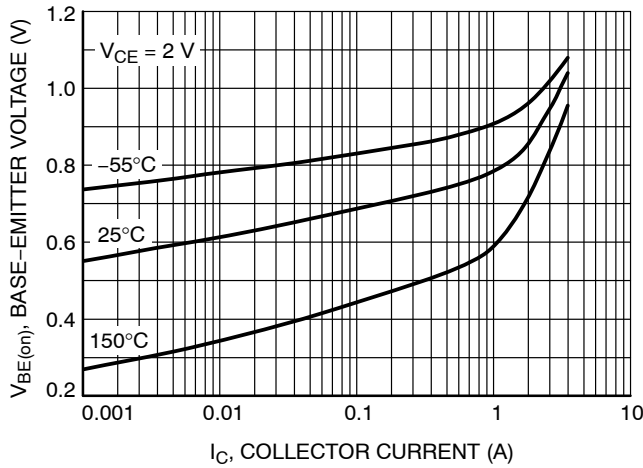


Figure 8. Base-Emitter Voltage

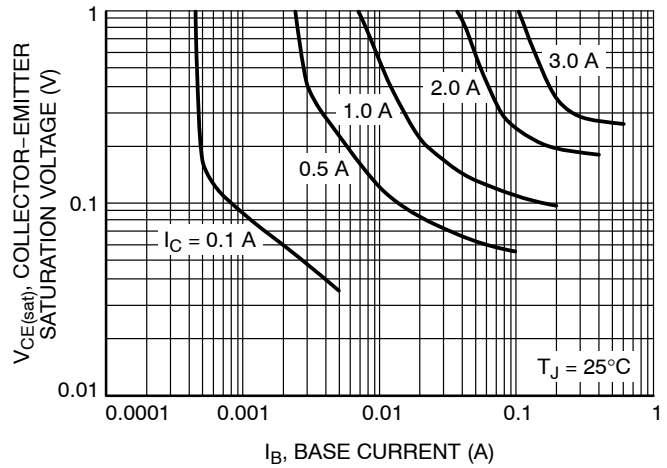


Figure 9. Collector Saturation Region

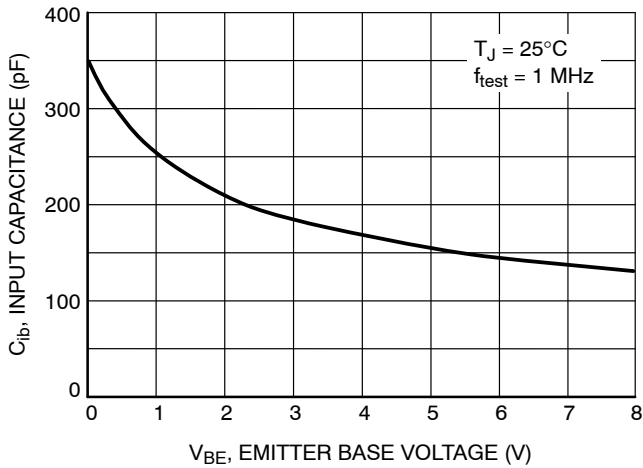


Figure 10. Input Capacitance

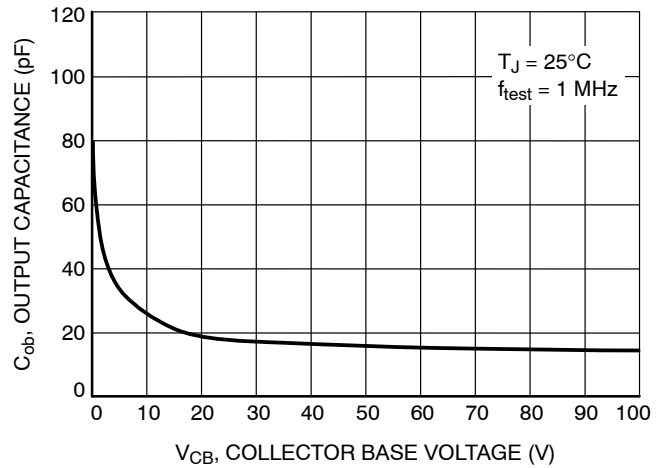


Figure 11. Output Capacitance

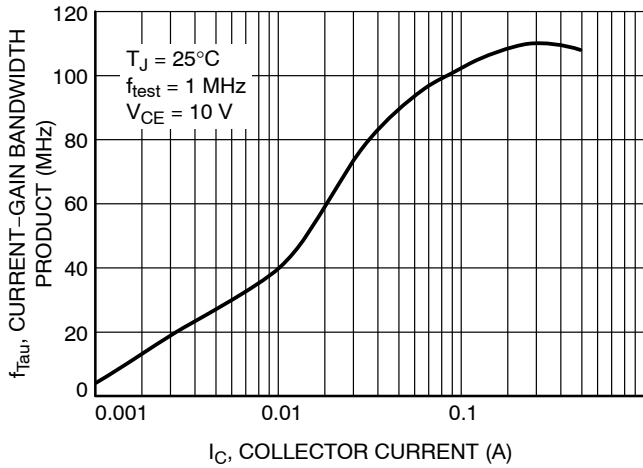


Figure 12. Current-Gain Bandwidth Product

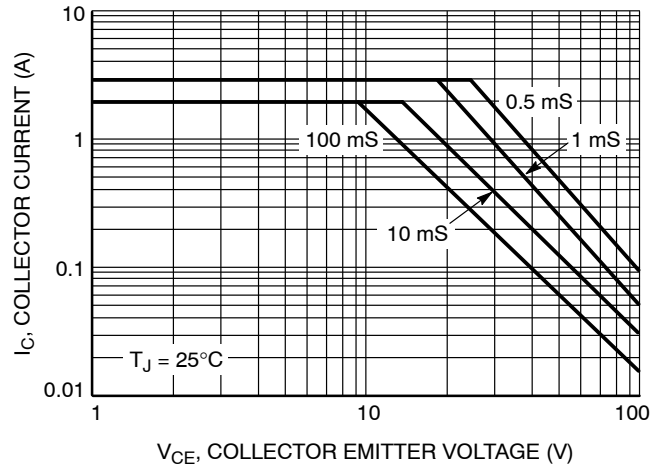
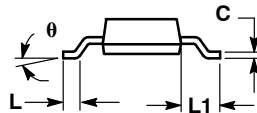
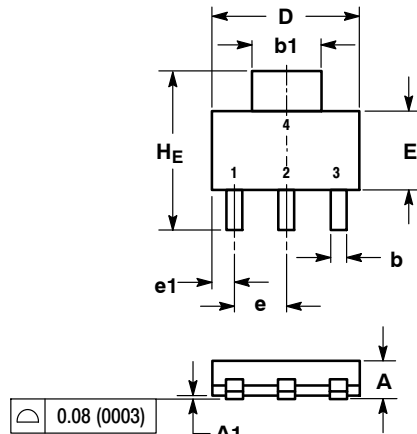


Figure 13. Safe Operating Area

# NSS1C200MZ4

## PACKAGE DIMENSIONS

SOT-223 (TO-261)  
CASE 318E-04  
ISSUE N

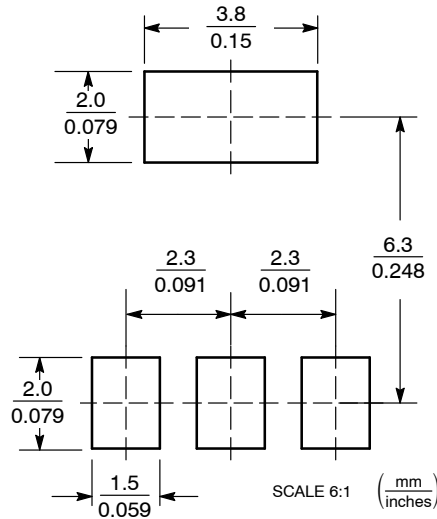


NOTES:  
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.  
2. CONTROLLING DIMENSION: INCH.


DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	---	---	0.008	---	---
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
theta	0°	---	10°	0°	---	10°

STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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